



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yeo, *et al.* Docket No.: TSM03-0555
Serial No.: 10/628,020 Art Unit: 2811
Filed: July 25, 2003 Examiner: TBD
For: Capacitor With Improved Capacitance Density and Method of Manufacture

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Respectfully submitted,


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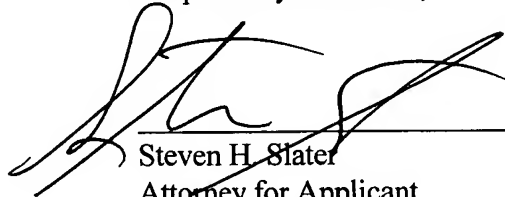
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The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A & 08B that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits.

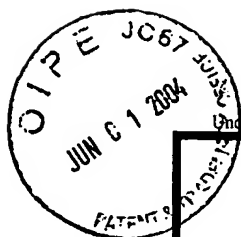
Respectfully submitted,



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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/628,020
				Filing Date	July 25, 2003
				First Named Inventor	Yeo, et al.
				Art Unit	2811
				Examiner Name	TBD
Sheet	1	of	5	Attorney Docket Number	TSM03-0555

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
	1	US-4,314,269	02-02-1982	Fujiki	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
	3	US-4,946,799	08-07-1990	Blake, et al.	
	4	US-5,447,884	09-05-1995	Fahey, et al.	
	5	US-5,461,250	10-24-1995	Burghartz, et al.	
	6	US-5,534,713	07-09-1996	Ismail, et al.	
	7	US-5,629,544	05-13-1997	Voldman, et al.	
	8	US-5,714,777	02-03-1998	Ismail, et al.	
	9	US-5,763,315	06-09-1998	Benedict, et al.	
	10	US-5,811,857	09-22-1998	Assaderaghi, et al.	
	11	US-6,008,095	12-28-1999	Gardner, et al.	
	12	US-6,015,993	01-18-2000	Voldman, et al.	
	13	US-6,046,487	04-04-2000	Benedict, et al.	
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	17	US-6,291,321 B1	09-18-2001	Fitzgerald	
	18	US-6,294,834 B1	09-25-2001	Yeh, et al.	
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	21	US-6,413,802 B1	07-02-2002	Hu, et al.	
	22	US-6,414,355 B1	07-02-2002	An, et al.	

FOREIGN PATENT DOCUMENTS						
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				Application Number	10/628,020
				Filing Date	July 25, 2003
				First Named Inventor	Yeo, <i>et al.</i>
				Art Unit	2811
				Examiner Name	TBD
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				Application Number	10/628,020
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				First Named Inventor	Yeo, <i>et al.</i>
				Group Art Unit	2811
				Examiner Name	TBD
				Attorney Docket Number	TSM03-0555
Sheet	4	of	5		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
	45	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.		
	46	SCHÜPPEN, A., <i>et al.</i> , "Mesa and Planar SiGe-HBTs on MBE-Wafers," Journal of Materials Science: Materials in Electronics, Vol. 6, (1995), pp. 298-305.		
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	48	HUANG, X., <i>et al.</i> , "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pp. 880-886.		
	49	SHAHIDI, G.G., "SOI Technology for the GHz Era," IBM J. Res. & Dev., Vol. 46, No. 2/3, March/May 2002, pp. 121-131.		
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	55	WELSER, J., <i>et al.</i> , "NMOS and PMOS Transistors Fabricated in Strained Silicon/Relaxed Silicon-Germanium Structures," IEDM 1992, pp. 1000-1002.		
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	57	"Future Gate Stack," International Sematech, 2001 Annual Report.		
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
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	32	ISMAIL, K., <i>et al.</i> , "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.		
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	34	GAMIZ, F., <i>et al.</i> , "Strained-Si/SiGe-on-Insulator Inversion Layers: The Role of Strained-Si Layer Thickness on Electron Mobility," Applied Physics Letters, Vol. 80, No. 22, (June 3, 2002), pp. 4160-4162.		
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	40	MAITI, C.K., <i>et al.</i> , "Film Growth and Material Parameters," Application of Silicon-Germanium Heterostructure, Institute of Physics Publishing, Ch. 2 (2001) pp. 32-42.		
	41	TIWARI, S., <i>et al.</i> , "Hole Mobility Improvement in Silicon-on-Insulator and Bulk Silicon Transistors Using Local Strain," International Electron Device Meeting, (1997), pp. 939-941.		
	42	OOTSUKA, F., <i>et al.</i> , "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Applications," International Electron Device Meeting, (2000), pp. 575-578.		
	43	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – I. Misfit Dislocations," Journal of Crystal Growth, Vol. 27, (1974), pp. 118-125.		
	44	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – II. Dislocation Pile-Ups, Threading Dislocations, Slip Lines and Cracks," Journal of Crystal Growth, Vol. 29, (1975), pp. 273-280.		
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